

Saravanapriyan Sriraman

List of Publications by Year in descending order

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16
papers

1,201
citations

758635

12
h-index

940134

16
g-index

16
all docs

16
docs citations

16
times ranked

1089
citing authors

#	ARTICLE	IF	CITATIONS
1	Overview of atomic layer etching in the semiconductor industry. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	420
2	Mechanism of hydrogen-induced crystallization of amorphous silicon. <i>Nature</i> , 2002, 418, 62-65.	13.7	379
3	Coarse Master Equation from Bayesian Analysis of Replica Molecular Dynamics Simulations. <i>Journal of Physical Chemistry B</i> , 2005, 109, 6479-6484.	1.2	119
4	Coarse Nonlinear Dynamics and Metastability of Filling-Emptying Transitions: Water in Carbon Nanotubes. <i>Physical Review Letters</i> , 2005, 95, 130603.	2.9	49
5	Evolution of structure, morphology, and reactivity of hydrogenated amorphous silicon film surfaces grown by molecular-dynamics simulation. <i>Applied Physics Letters</i> , 2001, 78, 2685-2687.	1.5	47
6	Hydrogen-induced crystallization of amorphous silicon thin films. I. Simulation and analysis of film postgrowth treatment with H ₂ plasmas. <i>Journal of Applied Physics</i> , 2006, 100, 053514.	1.1	38
7	Hydrogen-induced crystallization of amorphous Si thin films. II. Mechanisms and energetics of hydrogen insertion into Si-Si bonds. <i>Journal of Applied Physics</i> , 2006, 100, 053515.	1.1	29
8	Mechanism and activation energy barrier for H abstraction by H(D) from a-Si:H surfaces. <i>Surface Science</i> , 2002, 515, L469-L474.	0.8	27
9	Growth and characterization of hydrogenated amorphous silicon thin films from SiH ₂ radical precursor: Atomic-scale analysis. <i>Journal of Applied Physics</i> , 2004, 95, 1792-1805.	1.1	21
10	Mechanisms and energetics of SiH ₃ adsorption on the pristine Si(001)-(2 \times 1) surface. <i>Chemical Physics Letters</i> , 2001, 344, 249-255.	1.2	19
11	In Situ Probing and Atomistic Simulation of a-Si:H Plasma Deposition. <i>Materials Research Society Symposia Proceedings</i> , 2001, 664, 111.	0.1	17
12	Atomic-scale analysis of deposition and characterization of a-Si:H thin films grown from SiH radical precursor. <i>Journal of Applied Physics</i> , 2002, 92, 842-852.	1.1	12
13	Atomic-scale analysis of fundamental mechanisms of surface valley filling during plasma deposition of amorphous silicon thin films. <i>Surface Science</i> , 2005, 574, 123-143.	0.8	11
14	Mechanism and energetics of dimerization of SiH ₂ radicals on H-terminated Si(0)-(2 \times 1) surfaces. <i>Surface Science</i> , 2003, 540, L623-L630.	0.8	6
15	Computational modelling of atomic layer etching of chlorinated germanium surfaces by argon. <i>Physical Chemistry Chemical Physics</i> , 2019, 21, 5898-5902.	1.3	6
16	Surface Processes during Growth of Hydrogenated Amorphous Silicon. <i>Materials Research Society Symposia Proceedings</i> , 2004, 808, 311.	0.1	1